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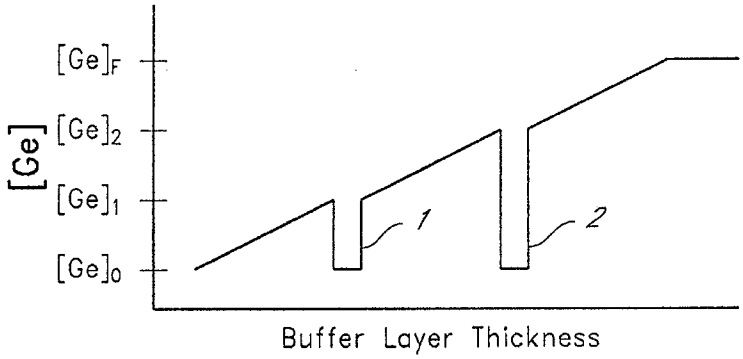
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(54) Title: STRAINED LAYERS WITHIN SEMICONDUCTOR BUFFER STRUCTURES



(57) Abstract: A semiconductor workpiece including a substrate 10, a relaxed buffer layer 14, 18 including a graded portion formed on the substrate, and at least one strained transitional layer 16 within the graded portion of the relaxed buffer layer 14, 18 and method of manufacturing the same. The at least one strained transitional layer 16 reduces an amount of workpiece bow due to differential coefficient of thermal expansion (CTE) contraction of the relaxed buffer layer 14, 18 relative to CTE contraction of the substrate 10.

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